

PBSS4160T-Q

60 V, 1 A NPN low VCEsat (BISS) transistor

15 December 2021

Product data sheet

1. General description

NPN low V_{CEsat} transistor in a small SOT23 plastic package. PNP complement: PBSS5160T-Q.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- · High efficiency, reduces heat generation
- · Reduces printed-circuit board area required
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Major application segments:
 - Automotive 42 V power
 - · Telecom infrastructure
 - · Industrial.
- Power management:
 - · DC-to-DC conversion
 - · Supply line switching.
- Peripheral driver
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors).

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	60	V
Ic	collector current		[1]	-	-	1	Α
I _{CM}	peak collector current	or limited by $T_{j(max)}$; $t_p = 1 \text{ ms}$		-	-	2	А
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	200	250	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	C
2	Е	emitter		J
3	С	collector		В — (
			SOT23	 E sym123

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4160T-Q		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4160T-Q	%U5

[1] % = placeholder for manufacturing site code

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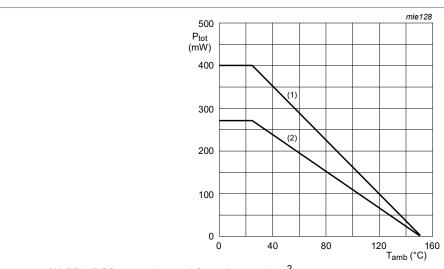
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	80	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current		[1]	-	0.9	А
			[2]	-	1	А
I _{CM}	peak collector current	or limited by T _{j(max)} ; t _p = 1 ms		-	2	Α
I _B	base current			-	300	mA
I _{BM}	peak base current	$t_p \le 300 \text{ μs; } \delta \le 0.02$		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	270	mW
			[2]	-	400	mW
			[1] [3]	-	1.25	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Pulsed; $t_p \le 10 \text{ ms}$; $\delta \le 0.02$



- (1) FR4 PCB mounting pad for collector 1 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	465	K/W
	junction to ambient		[2]	-	-	312	K/W
			[1] [3]	-	-	100	K/W

- 1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Pulsed; $t_p \le 10 \text{ ms}$; $\delta \le 0.02$.

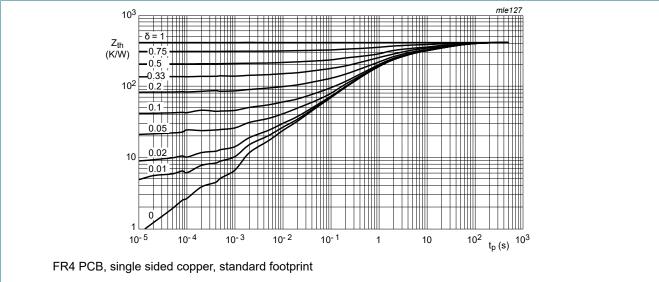


Fig. 2. Transient thermal impedance as a function of pulse time; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 60 V; I _E = 0 A; T _{amb} = 25 °C	-		-	100	nA
	current	V _{CB} = 60 V; I _E = 0 A; T _j = 150 °C	-		-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 60 V; V _{BE} = 0 V; T _{amb} = 25 °C	-		-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-		-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C	2	250	400	-	
		V_{CE} = 5 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	2	200	350	-	
		V_{CE} = 5 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	1	100	150	-	
V _{CEsat}	collector-emitter	I _C = 100 mA; I _B = 1 mA; T _{amb} = 25 °C	-		90	110	mV
	saturation voltage	I_C = 500 mA; I_B = 50 mA; T_{amb} = 25 °C	-		110	140	mV
		$I_C = 1 \text{ A}$; $I_B = 100 \text{ mA}$; pulsed; $t_p \le$	-		200	250	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-		200	250	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = 1 \text{ A}; I_B = 50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-		0.95	1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ A}; T_{amb} = 25 \text{ °C}$	-		0.82	0.9	V
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	1	50	220	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-		5.5	10	pF

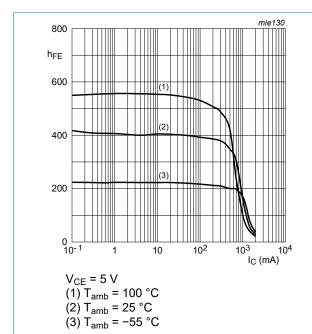


Fig. 3. DC current gain as a function of collector current; typical values

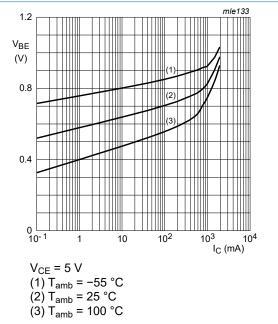
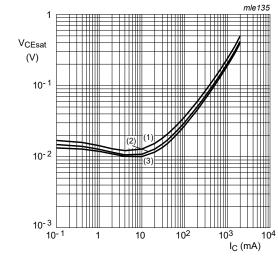


Fig. 4. Base-emitter voltage as a function of collector current; typical values

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$$I_{\rm C}/I_{\rm B} = 10$$

$$I_C/I_B = 10$$

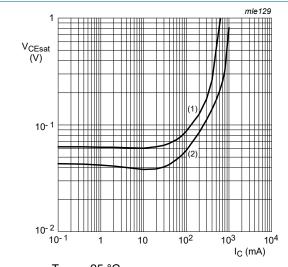
(1) $T_{amb} = 100 \,^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}\text{C}$$

(3) $T_{amb} = -55 \,^{\circ}\text{C}$

Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

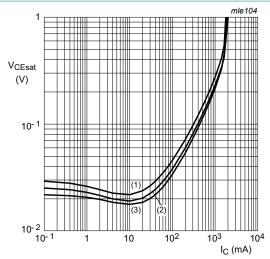


$$T_{amb} = 25 \,^{\circ}C$$

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

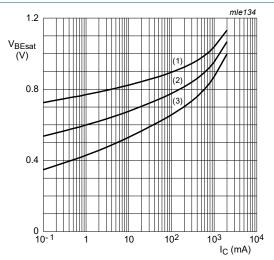
$$I_C/I_B = 20$$

(1) $T_{amb} = 100 \,^{\circ}C$

(2)
$$T_{amb} = 25 ^{\circ}C$$

(3) $T_{amb} = -55 ^{\circ}C$

Fig. 6. Collector-emitter saturation voltage as a function of collector curret; typical values



$$I_{\rm C}/I_{\rm B}=20$$

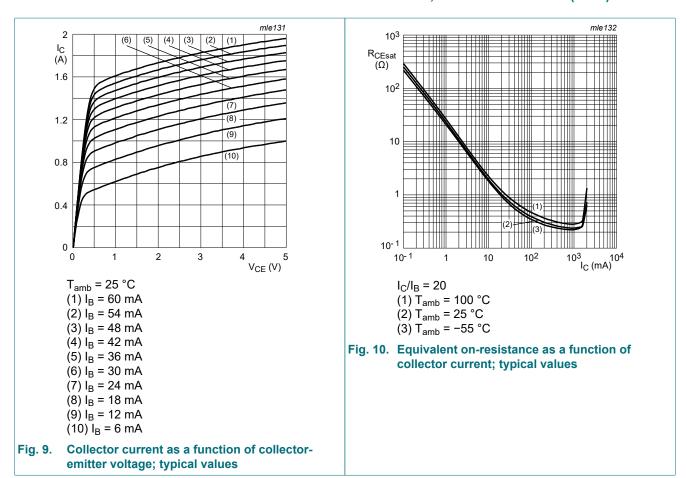
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

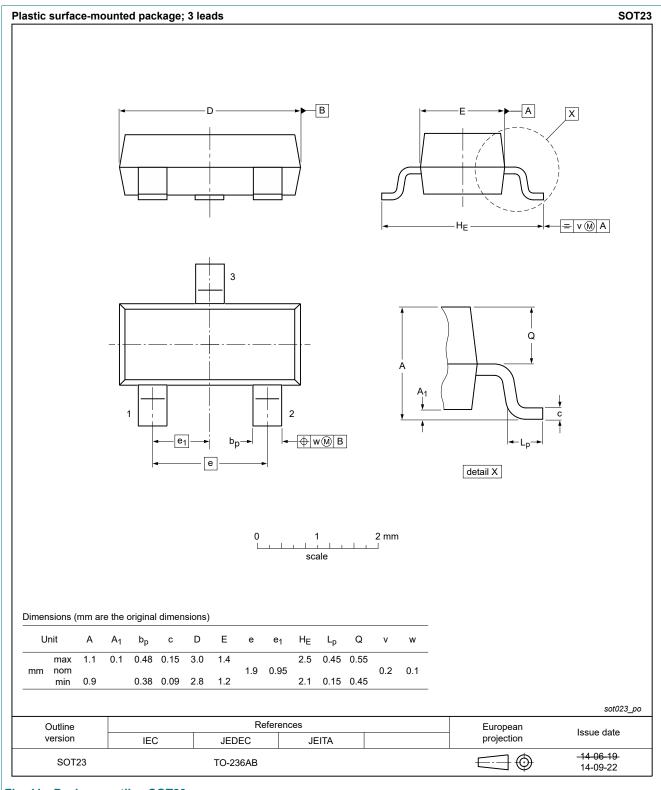
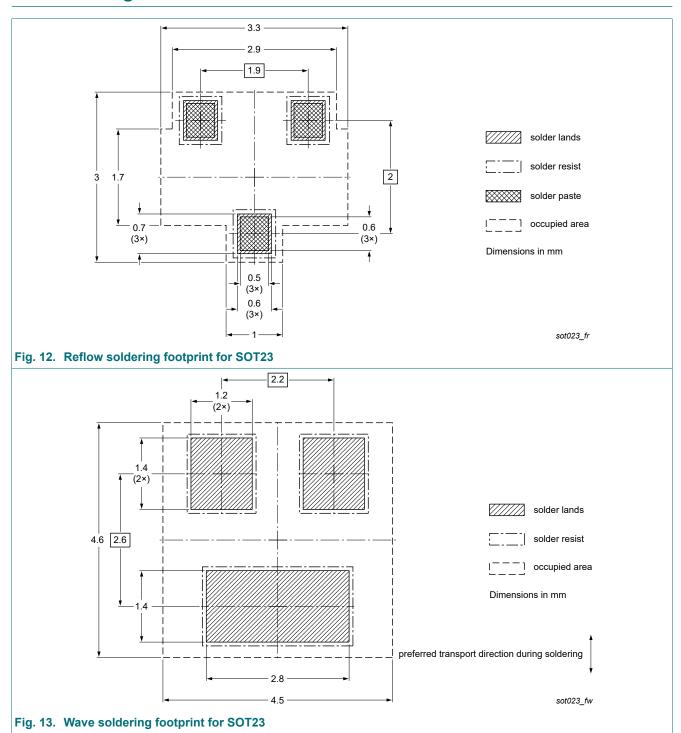


Fig. 11. Package outline SOT23

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160T-Q v.1	20211215	Product data sheet	-	-

60 V, 1 A NPN low VCEsat (BISS) transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 15 December 2021

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